2SB0621 (2SB621), 2SB0621A (2SB621A)

Silicon PNP epitaxial planar type

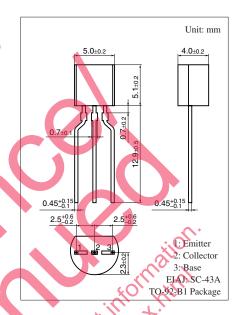
For low-frequency driver amplification Complementary to 2SD0592 (2SD592), 2SD0592A (2SD592A)

■ Features

- ullet Low collector-emitter saturation voltage $V_{CE(sat)}$
- High transition frequency f_T

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter		Symbol	Rating	Unit	
Collector-base voltage	2SB0621	V_{CBO}	-30	V	
(Emitter open)	2SB0621A		-60		
Collector-emitter voltage	2SB0621	V _{CEO}	-25	У	
(Base open)	2SB0621A		-50		
Emitter-base voltage (Coll	V _{EBO}	- 5	V		
Collector current	I_{C}	-1	A		
Peak collector current	I _{CP}	-1.5	A		
Collector power dissipation	Pc	750	mW		
Junction temperature	T_{j}	150	°C		
Storage temperature	T _{stg}	-55 to +15 0	°C		



■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage 2SB0621	V_{CBO}	$I_{\rm C} = -10 \mu{\rm A}, I_{\rm E} = 0$	-30			V
(Emitter open) 2SB0621A		"!!!?? O.,	-60			
Collector-emitter voltage 2SB0621	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-25			V
(Base open) 2SB0621A		colle corri	-50			
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\rm E} = -10 \text{GA}, I_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			- 0.1	μΑ
Forward current transfer ratio	hæi*	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	85		340	_
	h _{FE2}	$\dot{V}_{CE} = -5 \text{ V}, I_C = -1 \text{ A}$	50			_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF
(Common base, input open circuited)						

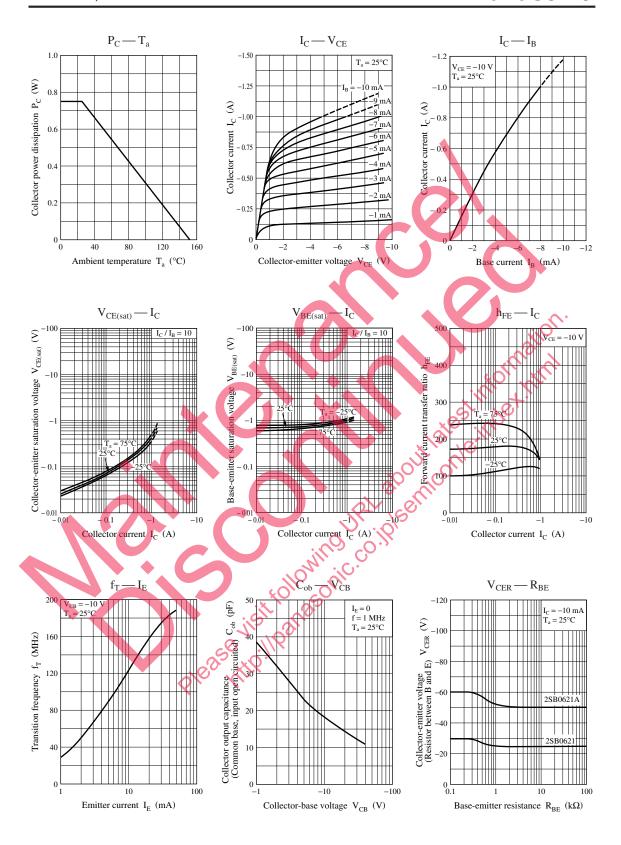
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

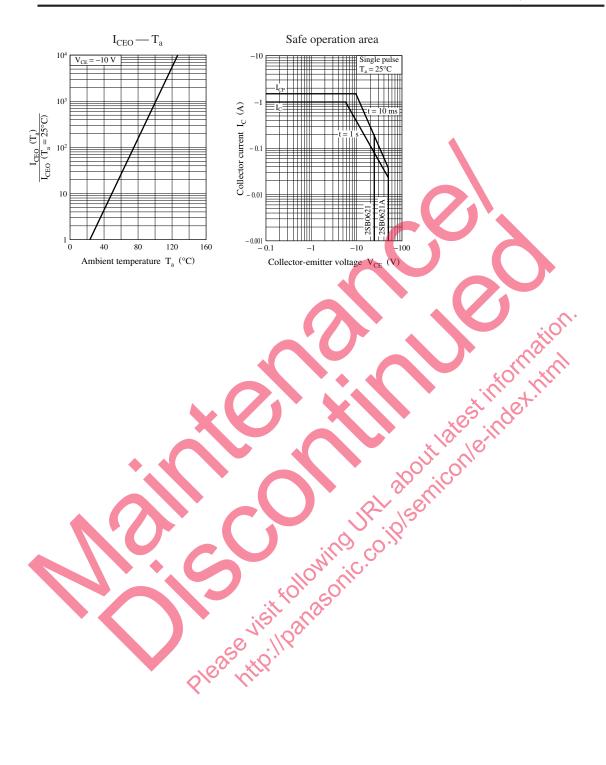
Rank	Q	R	S	
h _{FE1}	85 to 170	120 to 240	170 to 340	

Note) The part numbers in the parenthesis show conventional part number.

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